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**Barraud et al.**

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(54) **NANOWIRE AND PLANAR TRANSISTORS  
CO-INTEGRATED ON UTBOX SOI  
SUBSTRATE**

(2013.01); **H01L 27/1211** (2013.01); **H01L  
29/0669** (2013.01); **H01L 29/413** (2013.01);  
(Continued)

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CPC ..... **H01L 29/413**; **H01L 29/0669**  
USPC ..... **257/623**; **438/164**  
See application file for complete search history.

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(30) **Foreign Application Priority Data**

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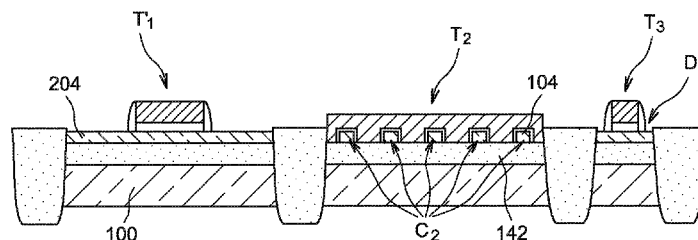
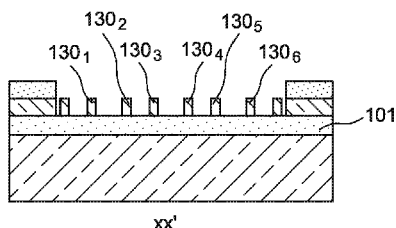
(57) **ABSTRACT**

(51) **Int. Cl.**  
**H01L 29/06** (2006.01)  
**H01L 21/84** (2006.01)  
(Continued)

Fabrication of a microelectronic device on a semiconductor  
on insulator type substrate, the device being provided with a  
transistor of a given type, the channel structure of which is  
formed from semiconducting bar(s), a dielectric area differ-  
ent from the insulating layer of the substrate being provided to  
replace the insulating layer, facing the transistor channel  
structure, specifically for this given type of transistor.

(52) **U.S. Cl.**  
CPC ..... **H01L 29/0673** (2013.01); **H01L 21/845**

**5 Claims, 15 Drawing Sheets**



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*H01L 29/41* (2006.01)  
*H01L 51/44* (2006.01)  
*H01L 29/786* (2006.01)  
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*H01L 29/78* (2006.01)
- (52) **U.S. Cl.**  
 CPC ..... *H01L 29/785* (2013.01); *H01L 29/78648*  
 (2013.01); *H01L 29/78696* (2013.01); *H01L*  
*51/057* (2013.01); *H01L 51/444* (2013.01)

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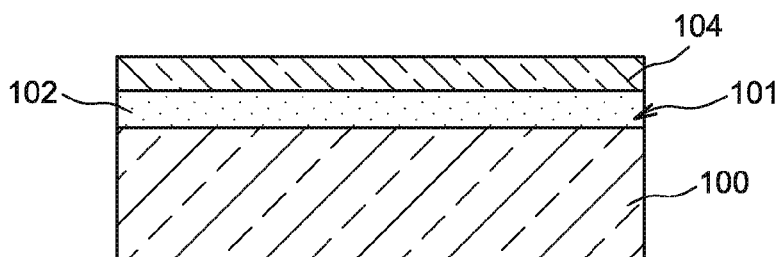
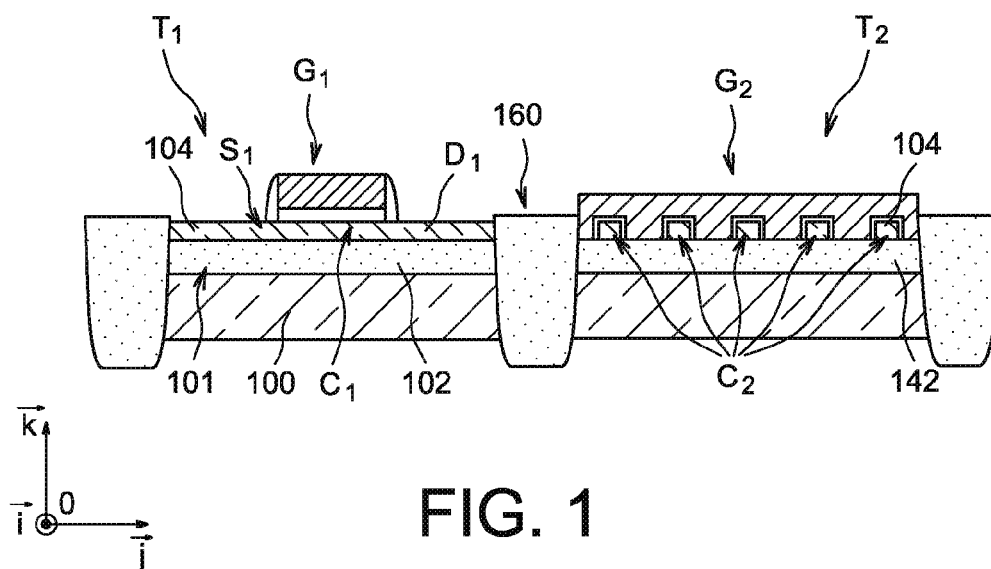
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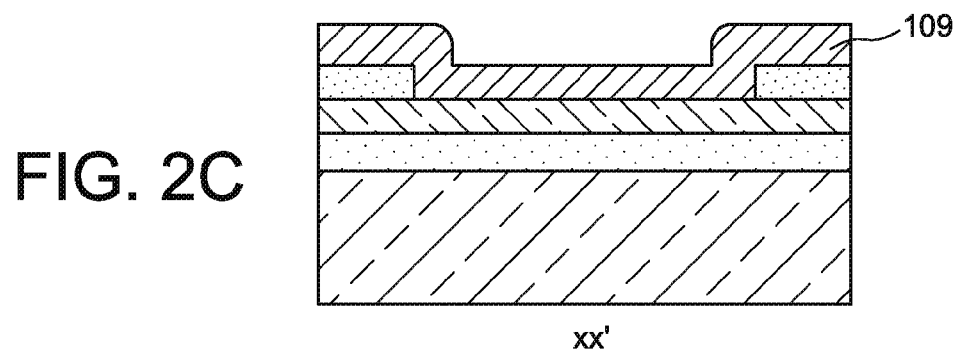
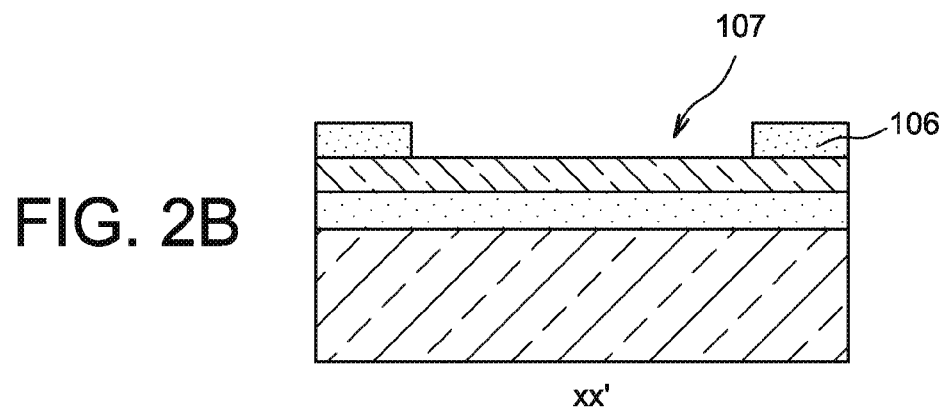
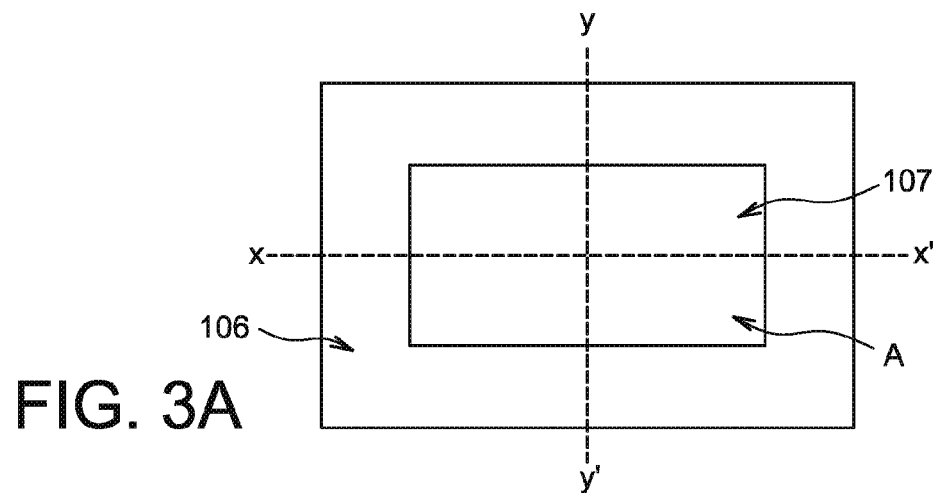


FIG. 3B

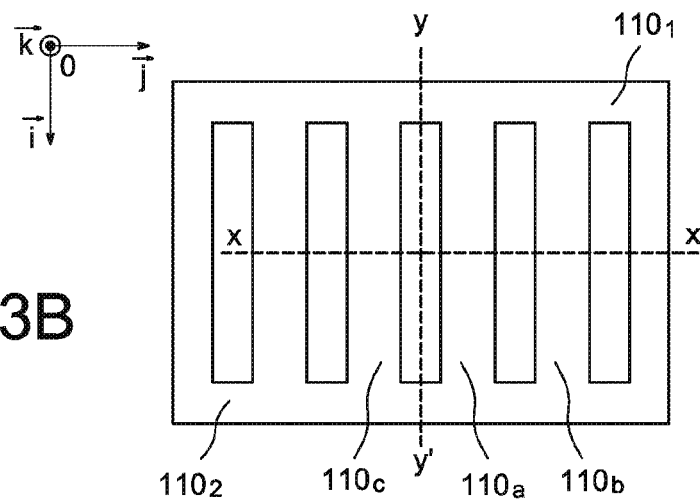


FIG. 2D

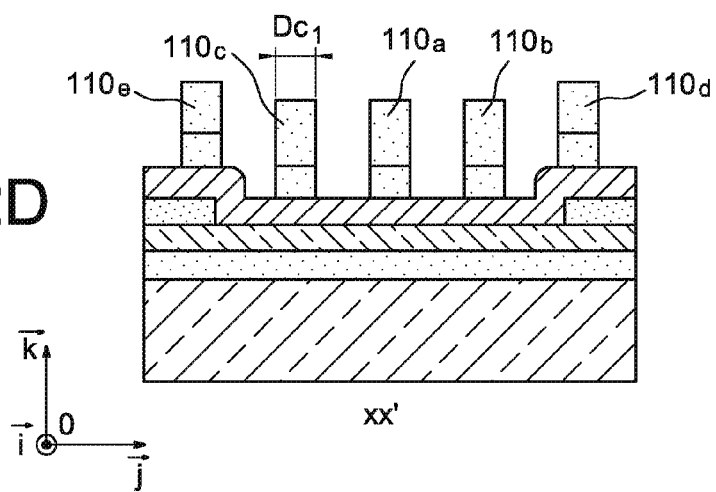
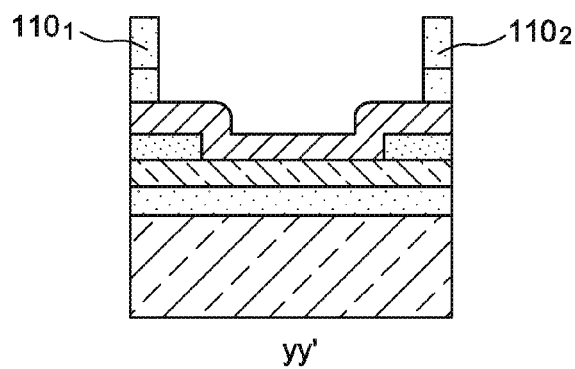


FIG. 4A



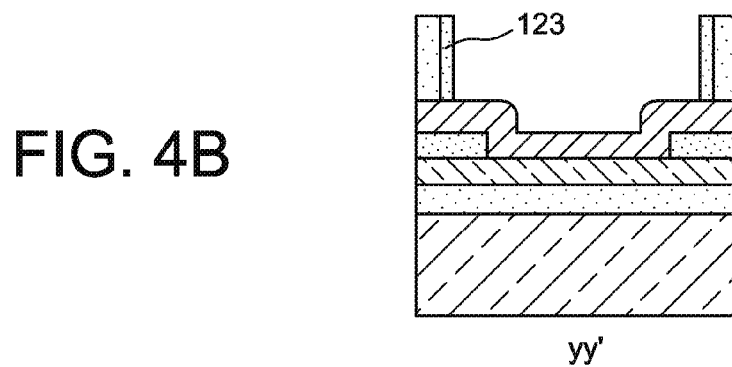
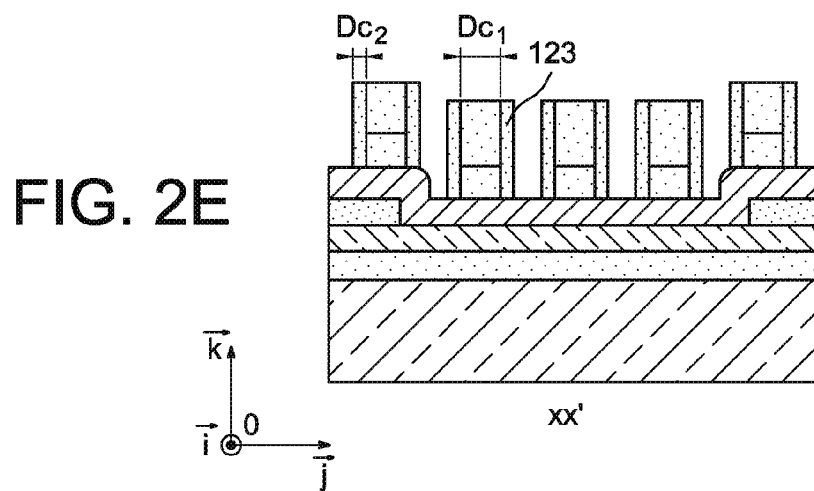
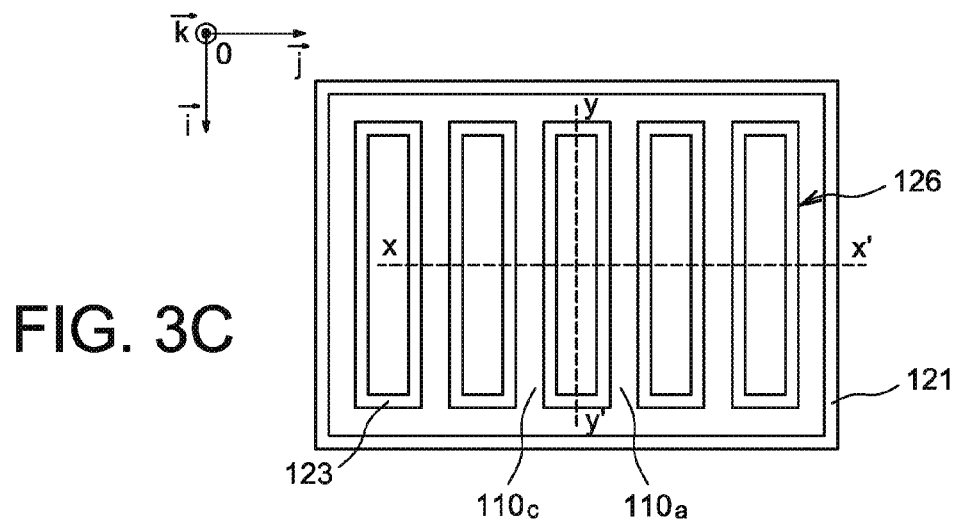


FIG. 3D

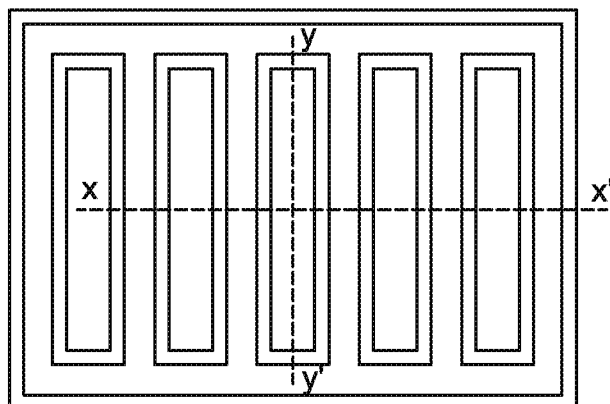


FIG. 2F

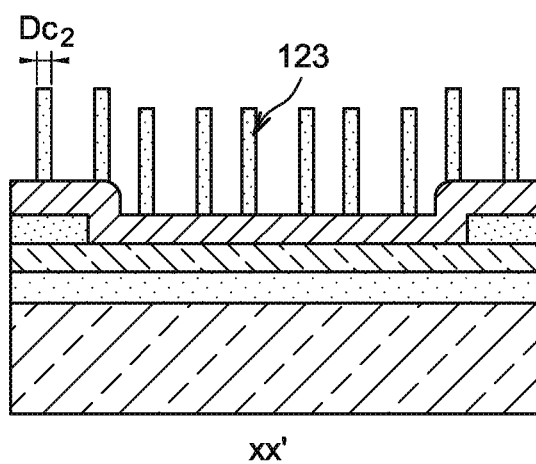


FIG. 4C

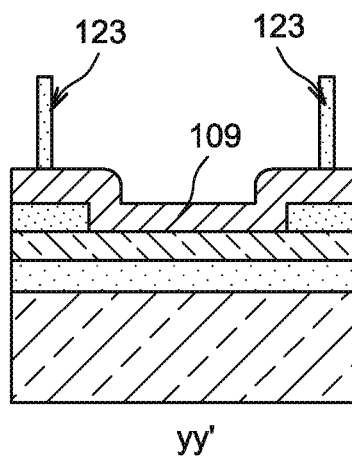


FIG. 3E

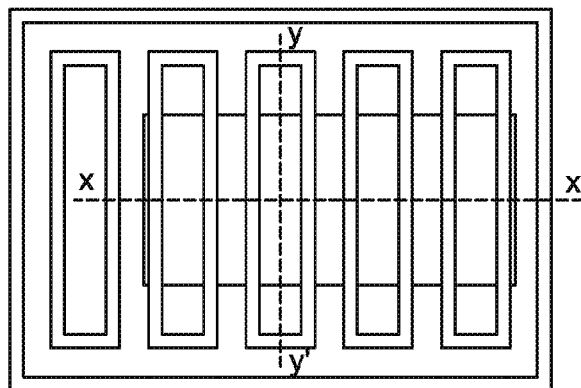


FIG. 2G

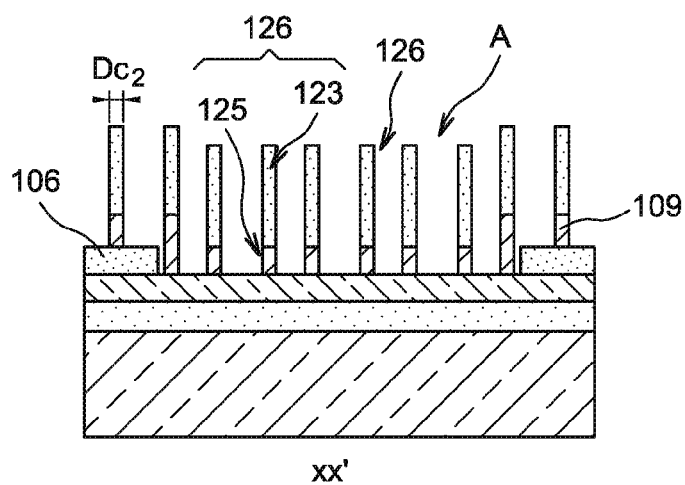


FIG. 4D

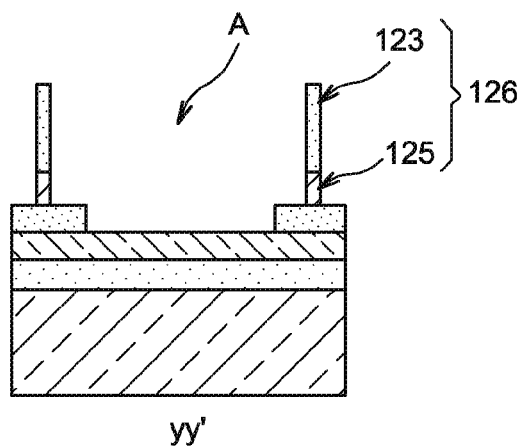




FIG. 3F

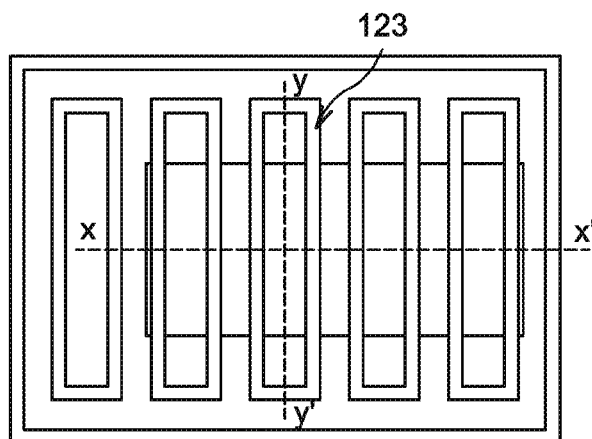


FIG. 2H

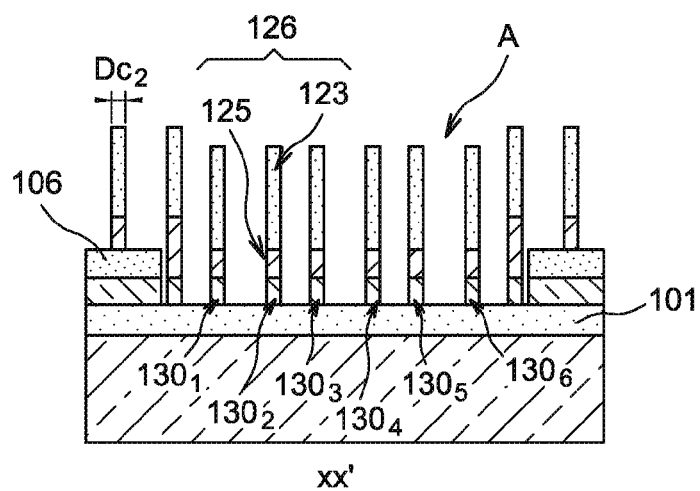


FIG. 4E

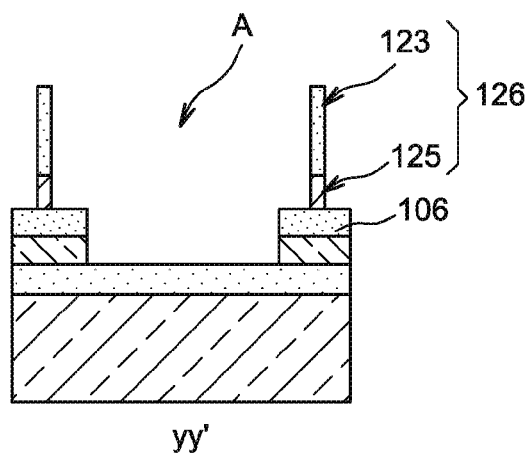


FIG. 3G

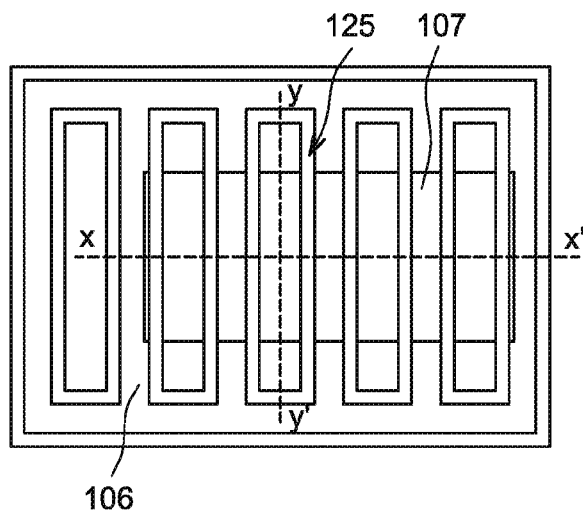


FIG. 2I

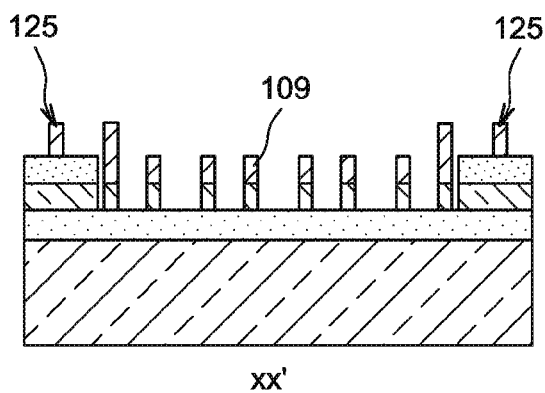


FIG. 4F

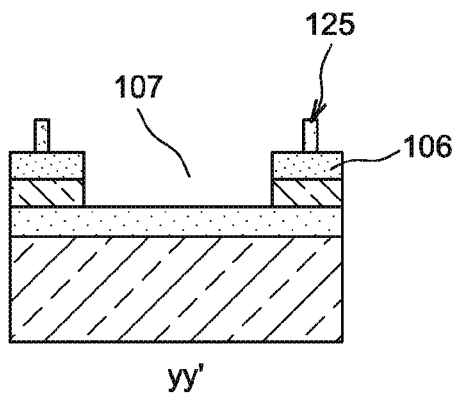


FIG. 3H

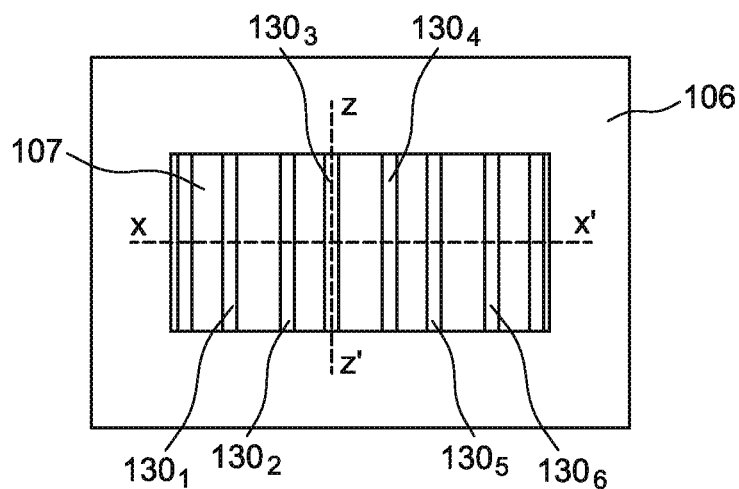


FIG. 2J

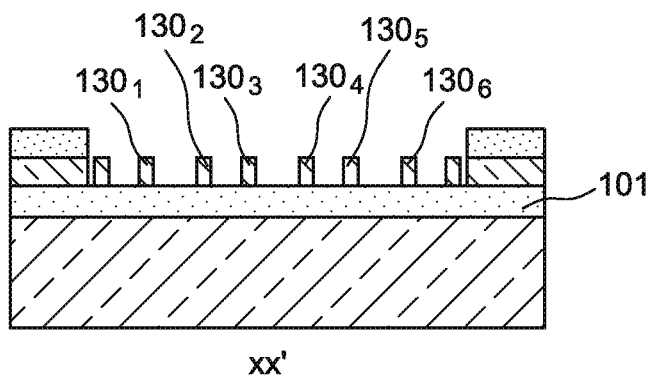


FIG. 4G

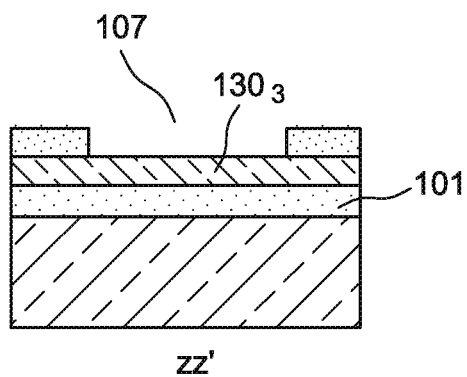


FIG. 3I

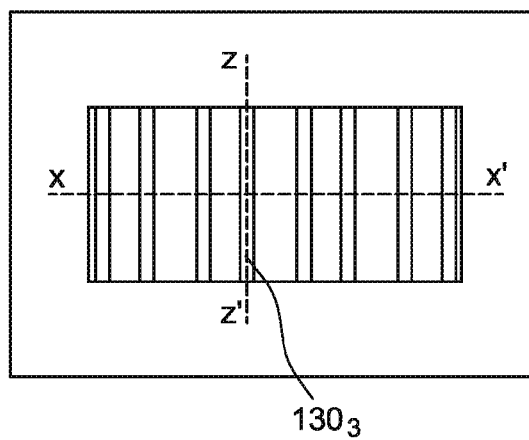


FIG. 2K

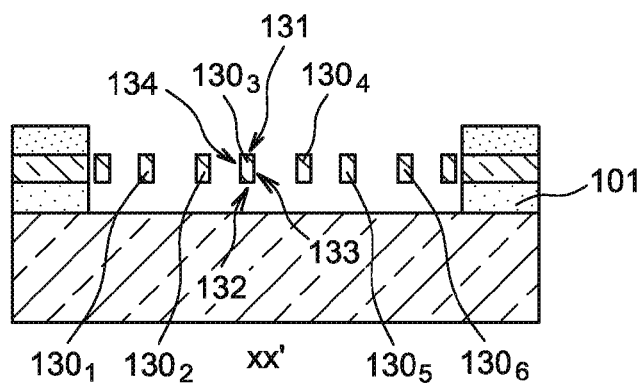


FIG. 4H

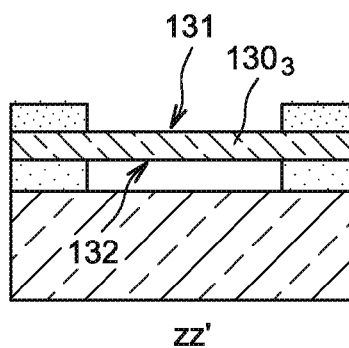


FIG. 3J

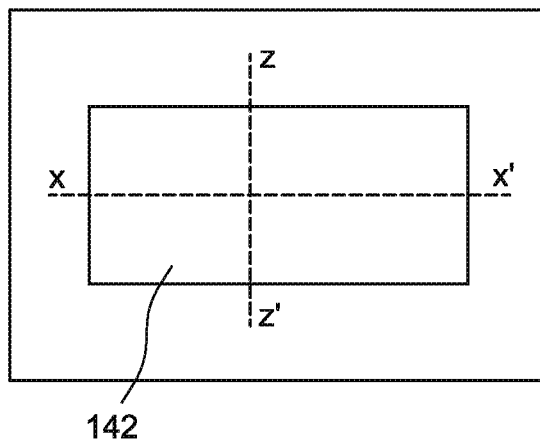


FIG. 2L

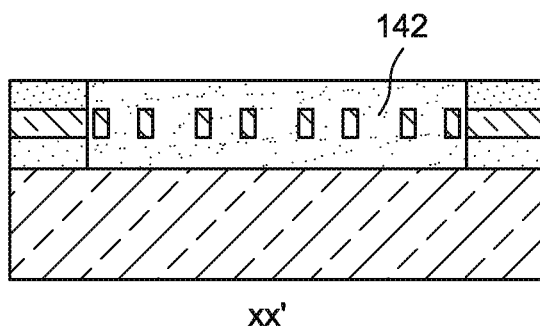


FIG. 4I

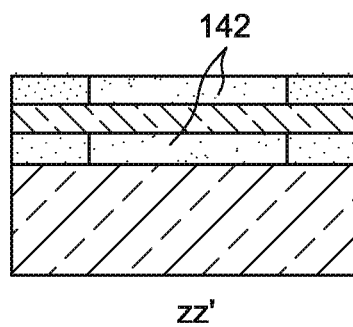


FIG. 3K

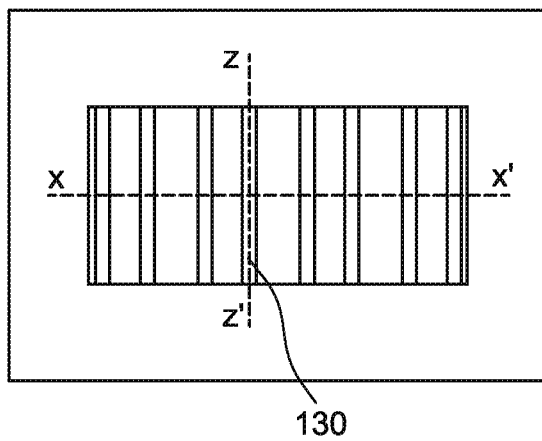


FIG. 2M

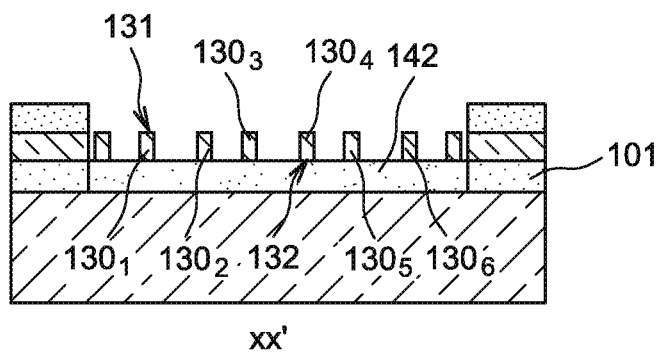


FIG. 4J

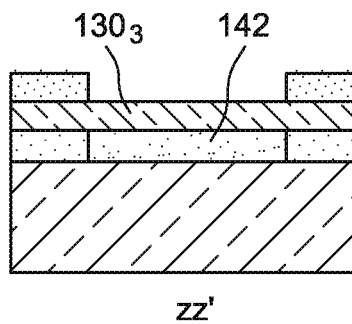


FIG. 2N

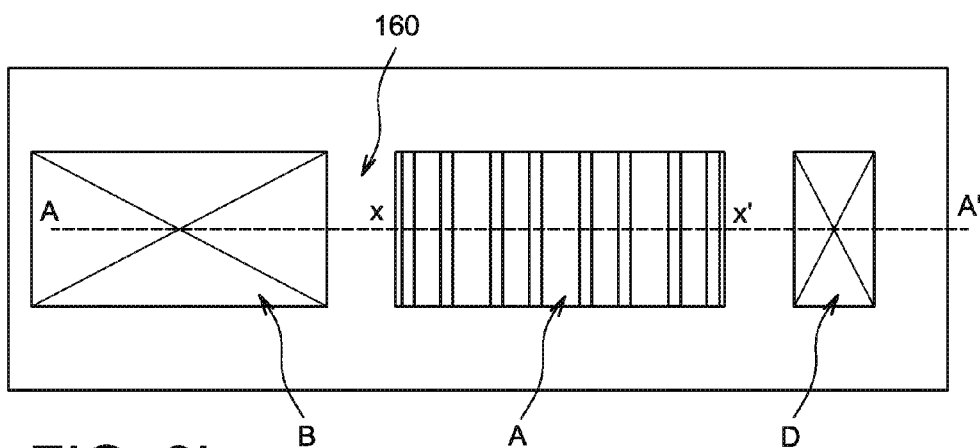
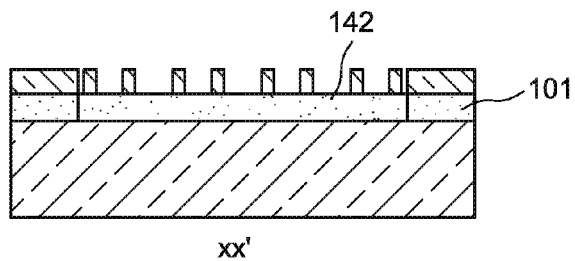


FIG. 3L

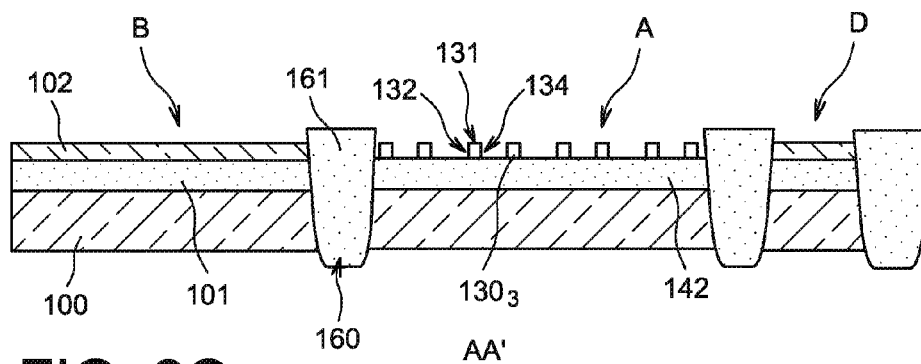
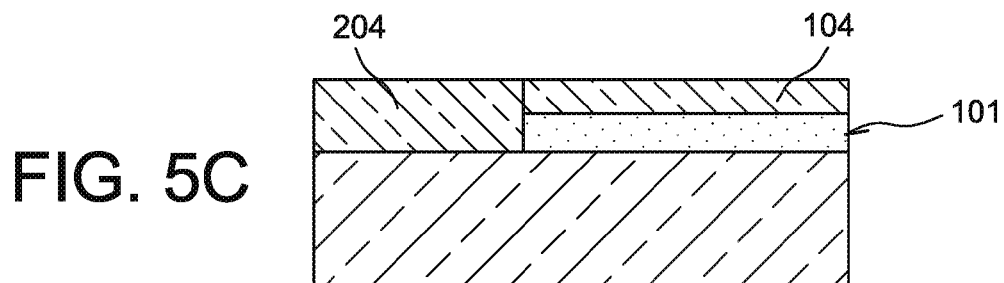
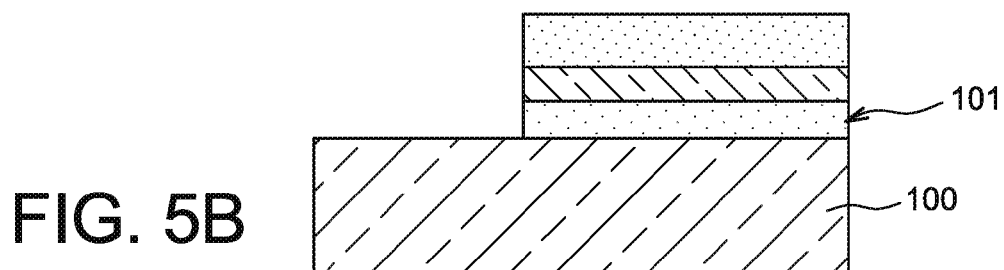
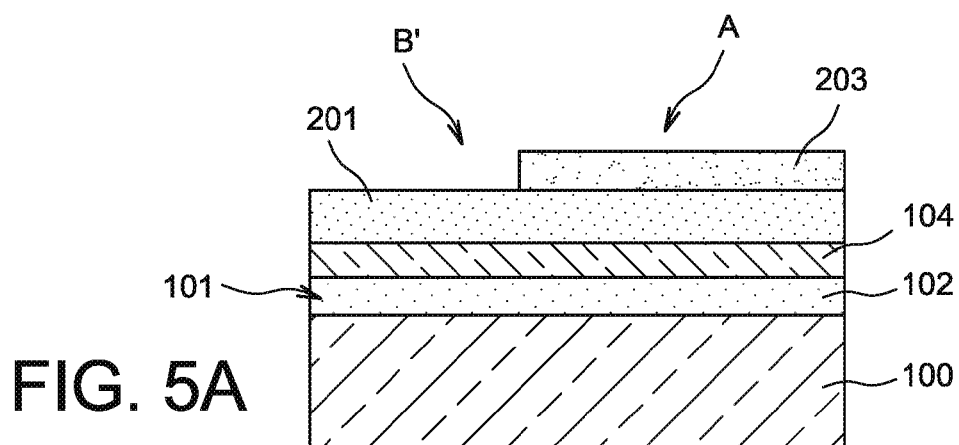
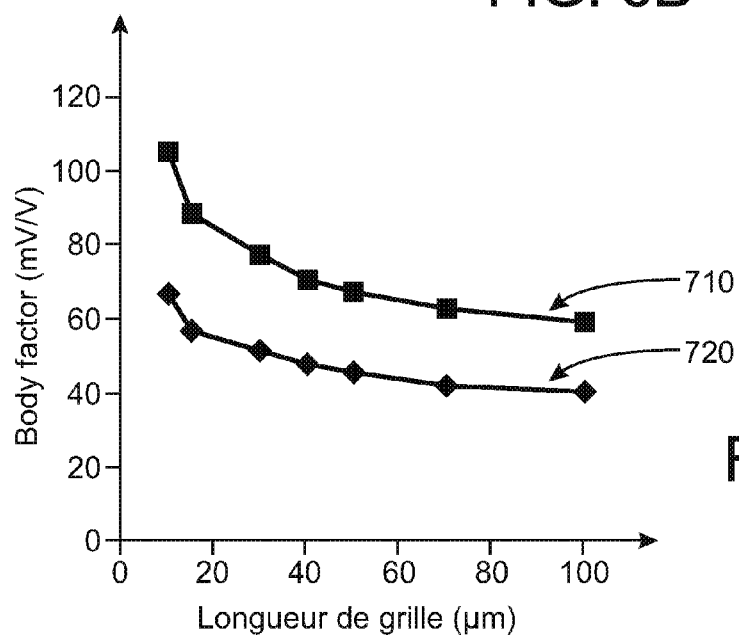
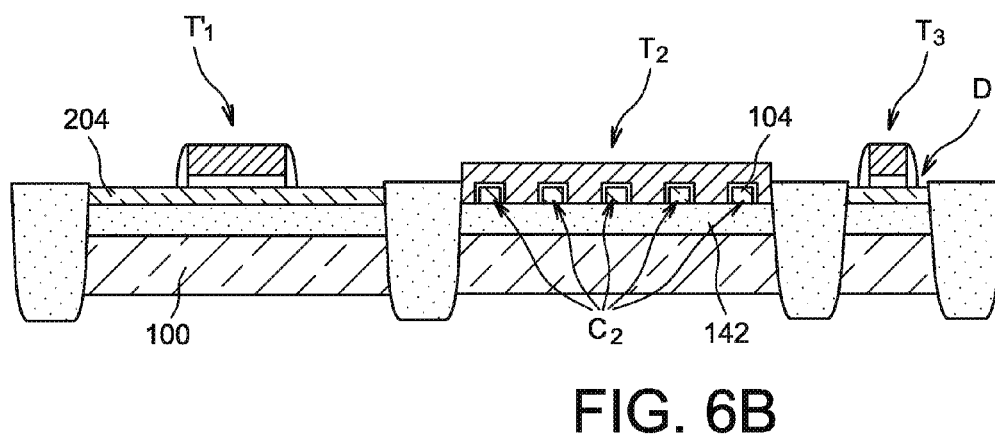
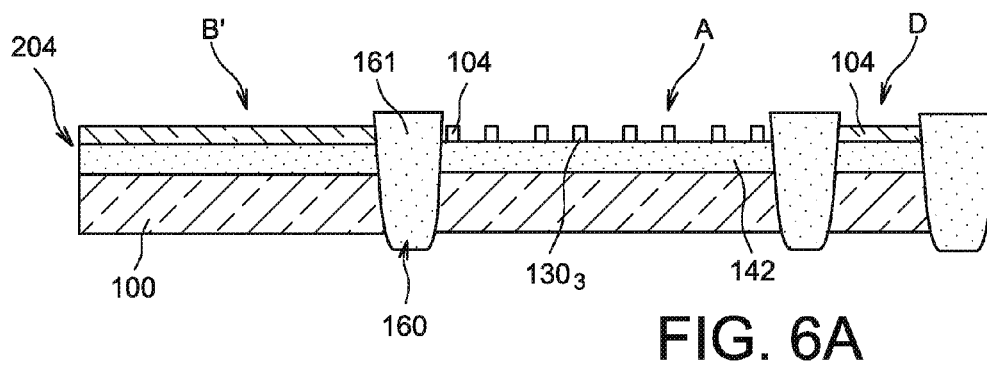


FIG. 2O







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# NANOWIRE AND PLANAR TRANSISTORS CO-INTEGRATED ON UTBOX SOI SUBSTRATE

## CROSS REFERENCE TO RELATED PATENT APPLICATIONS

The present application is a divisional application of U.S. application Ser. No. 14/266,999, filed May 1, 2014, now U.S. Pat. No. 9,276,073 issued Mar. 1, 2015, the entire contents of which are incorporated herein by reference. U.S. application Ser. No. 14/266,999 claims foreign priority to French Application No. 13 54045, filed May 2, 2013.

## DESCRIPTION

### 1. Technical Field

This invention relates to the field of microelectronics and is particularly applicable to producing of transistors for which the channel semiconducting structure is in the form of a plurality of parallel adjacent semiconducting nanowires on a semiconductor on insulator type substrate.

In particular, it can be used to make different types of transistors on a single semiconductor on insulator substrate in which one or several regions have been modified.

The invention is applicable for example to the use of fin-FET or trigate type transistors co-integrated on the same semiconductor on insulator substrate as FDSOI type planar gate transistors.

### 2. Prior Art

New transistor structures for which the channel is formed from one or several parallel semiconducting bars have been developed, particularly to increase the integration density in comparison with conventional MOSFET transistors.

For example, transistors of the type commonly called “fin-FET” comprise a channel formed from one or several semiconducting bars or fins in the form of adjacent nanowires that extend parallel to the substrate on which this or these nanowires are arranged.

Document “Spacer FinFET: nanoscale double-gate CMOS technology for the terabit era” by Choi et al., Solid-State Electronics, vol. 46, pp. 1595-1601, 2002) gives an example disclosure of a method for making a finFET transistor with small nanowires obtained by etching through a mask in which the patterns called “spacers” are formed by conforming deposition of a layer in contact with a sacrificial pad that is thinner than the critical dimension of the pad.

The gate structure of nanowire transistors is usually non-planar and is designed so as to encase the nanowire(s), and particularly to extend over the side faces of the nanowires.

For example, the transistor of the type commonly called “Trigate” has a partially encasing gate structure around one or several nanowires arranged in contact with the flanks of the nanowire(s) and on their top face.

Document U.S. Pat. No. 6,914,295 B2 discloses an example of a method for making such a tri-Gate transistor.

Unlike a planar gate structure for which the gate extends only in a direction parallel to the channel, the gate-channel contact surface is improved which has the main advantage of reducing leakage currents when the transistor is in the blocked or “off” state. Thus, shorter gate lengths can be obtained than with planar gate architectures, while maintaining exactly the same electrical performances.

Furthermore, in the field of planar gate structure transistors, transistors of the type commonly called FDSOI (FDSOI for “Fully Depleted Silicon On insulator”), made on a semiconductor on insulator type substrate have the advantage over

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conventional MOS transistors that they can have a threshold voltage  $V_T$  that can be modulated by electrostatic coupling also referred to as capacitive coupling.

This is done by varying the potential applied to the semiconducting support layer of the semiconductor on insulator type substrate on which these transistors are formed.

The coupling between this support layer and the transistor channel can be obtained by using an SOI substrate with a thin or ultra-thin layer of buried oxide (BOX).

However, this insulating layer may not be suitable for nanowire transistors.

The problem arises of finding a new method for making a transistor structure with semiconducting nanowires that is capable of co-integrating this structure on a semiconductor on insulator type substrate, with one or several transistors of a different type and particularly planar transistors.

## PRESENTATION OF THE INVENTION

This invention makes use of a microelectronic device on a semiconductor on insulator type substrate including the formation of at least one channel structure of at least one first type of transistor, said structure being formed by one or several adjacent semiconducting bars, on a given dielectric area that is different from the remainder of the insulating layer of the substrate.

A semiconductor on insulator type substrate means a substrate with a semiconducting support layer, an insulating layer on said support layer and said thin semiconducting layer being supported on said insulating layer.

To obtain the given dielectric area, the material in said insulating layer of the substrate is firstly removed in a region in which said semiconducting bars are located.

A replacement by a given dielectric material can then be made so as to make a replacement dielectric area different from the remainder of said insulating layer of the substrate, the thickness and composition of which may be adapted specifically to the first type of transistor.

Thus, this invention relates to a method for making a microelectronic device including steps as follows:

a) make one or several semiconducting bars, designed to form at least one transistor channel or several transistor channels of a first type, by etching through an opening in a first mask facing a given region of a thin semiconducting layer of a semiconductor on insulator substrate,

b) remove an area from said insulating layer of said substrate in extension of said opening so as to expose said semiconducting bars.

The semiconducting bars are also called “nanowires” when their critical dimension is less than 1  $\mu\text{m}$ .

The insulating layer is based on a material with a first dielectric constant  $k_1$ . According to one possible embodiment, the material of the insulating layer may be  $\text{SiO}_2$ .

Advantageously, the method also comprises a step after step b) consisting of depositing a given dielectric material facing said opening to replace said area of said insulating layer removed in b). The thickness and/or composition of this replacement dielectric material are different from the thickness and/or composition of said area of said insulating layer removed in step b).

Thus, a specific dielectric area is formed facing the semiconducting bars different from the initial insulating layer of the semiconductor on insulator type substrate.

Advantageously, the given dielectric replacement material is a dielectric material with a composition and thickness that are selected to enable electrostatic or capacitive coupling between said support layer and said conducting bars.

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According to one possible embodiment of the method, the given dielectric replacement material has a dielectric constant  $k_2$  such that  $k_2 > k_1$ .

In particular, this given replacement dielectric material may be  $\text{Si}_3\text{N}_4$  or a "high- $k$ " type dielectric.

Advantageously, at least one isolation trench may be made between said given region and said other region in the thin semiconducting layer. This isolation trench may be of the STI (Shallow Trench Isolation) type.

Advantageously, the semiconducting bar(s) is (are) formed in step a) by etching the thin semiconducting layer through one or several blocks of a second mask partially covering said opening of said first mask and made by:

forming one or several sacrificial pads with critical dimension  $\text{Dc}_1$  given on said given region,

forming one or several blocks with critical dimension  $\text{Dc}_2 < \text{Dc}_1$  in contact with the flanks of said pad(s),

removing said sacrificial pad(s).

Thus, small semiconducting bars can be made.

The method may further include deposition of a hard mask layer on said first mask and in said opening, before production of said mask.

In this case, production of said second mask may also include anisotropic etching of the hard mask layer through said blocks with critical dimension  $\text{Dc}_2$ .

The blocks of the second mask may have one end supported on the first mask and that is outside a region delimited by said opening of said first mask. This arrangement can be used to facilitate subsequent removal of the second mask.

According to one possible embodiment of the method, in step b) another area of said insulating layer facing another region of said thin semiconducting layer may be protected by said first mask and kept.

Facing this other area, at least one transistor of a second type, different from said first type, may be provided.

Said other area of said insulating layer that was kept may have a thickness and a composition adapted to the second type of transistor.

Thus, according to the invention, co-integration of transistors of the first type for which the channel is formed by adjacent parallel bars facing said specific dielectric area, and at least one transistor of a second type, different from the first type, may be made facing said intact conserved area of said insulating layer.

The transistor of the first type may for example be a tri-gate or finFET type transistor with an encasing gate structure, while the transistor(s) of the second type may for example be made from MOS transistors with a planar gate structure.

Advantageously, said insulating layer of the substrate may be thin or ultra-thin with a thickness of less than 20 nm. Thus, according to one possible embodiment, the transistor(s) of the second type may for example be of the FDSOI type.

According to another aspect, this invention also relates to a microelectronic device provided with:

a substrate comprising a thin semiconducting layer supported on an insulating layer, said insulating layer being supported on a semiconducting support layer,

at least one first transistor of a first type comprising a region adapted to form a channel formed from one or several adjacent bars in and/or on said thin semiconducting layer and an encasing gate arranged on said bars and around the lateral faces of said bars, said channel of said first transistor being arranged above and facing a modified area of the substrate, or on a modified area of the substrate or on a modified area of the substrate based on a dielectric material different from the material in the insulating layer.

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The dielectric constant  $k_2$  of the given dielectric material in the modified area of the substrate may be such that  $k_2 > k_1$  where  $k_1$  is the dielectric constant of the material of said insulating layer.

The given dielectric material of the modified area of the substrate may also have a composition and thickness selected to enable capacitive coupling between said channel of said first transistor and said semiconducting support layer.

This in particular makes it possible to modulate the threshold voltage of said first transistor.

The insulating layer of the substrate may be based on  $\text{SiO}_2$  and its thickness may be less than 25 nm or 20 nm. Thus, the substrate may have an UTBOX type of insulating layer.

Advantageously, the device may comprise at least one second transistor, the channel area of which is formed in a region of the thin semiconducting layer arranged on and in contact with said insulating layer of the substrate.

The composition and thickness of the insulating layer may be designed to enable capacitive coupling between the channel of said second transistor and said semiconducting support layer of said substrate.

Advantageously, the device may further comprise at least one other transistor, in which the channel area is formed in a semiconducting region arranged on and in contact with the semiconducting support layer of the substrate.

#### BRIEF DESCRIPTION OF THE DRAWINGS

This invention will be better understood after reading the description of example embodiments given purely for information and that are in no way limitative, with reference to the appended drawings in which:

FIG. 1 shows an example of a microelectronic device implemented according to the invention on a semiconductor on insulator substrate, including an adjacent nanowire transistor supported on a first insulating region and a planar gate structure transistor supported on a second insulating region forming part of the insulating layer of said substrate;

FIGS. 2A-2O, 3A-3L, 4A-4J show an example of a method according to an example embodiment of a microelectronic transistor device provided with at least one nanowire transistor and at least one planar gate structure transistor co-integrated on an SOI substrate;

FIGS. 5A-5C, and 6A-6B show an example embodiment of a microelectronic transistor device provided with at least one nanowire transistor on a dielectric area replacing the insulating layer of an SOI substrate of a substrate and at least one other transistor on a semiconducting region replacing the thin semiconducting layer and the insulating layer of the SOI substrate;

FIG. 7 shows parameter variation curves illustrating a variation of the threshold voltage of a nanowire transistor on a dielectric area of silicon nitride or on a silicon oxide area as a function of its gate length;

Identical, similar or equivalent parts of the different figures have the same numeric references to facilitate comparison between different figures.

The different parts shown in the figures are not necessarily all at the same scale, in order to make the figures more easily readable.

#### DETAILED PRESENTATION OF PARTICULAR EMBODIMENTS

FIG. 1 shows a microelectronic device formed from a semiconductor on insulator substrate including a semiconducting support layer 100, a thin insulating layer 101

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arranged on and in contact with the semiconducting support layer **100** and a thin semiconducting layer **104** arranged on and in contact with the insulating layer **101**.

In a first region of the substrate, a transistor  $T_1$  of a given type, for example a MOSFET FDSOI, comprises a channel  $C_1$  and source regions  $S_1$  and drain regions  $D_1$  formed in said thin semiconducting layer **104**. The gate  $G_1$  of this transistor has a planar structure in the sense that it is in the form of an area extending parallel to the principal plane of the substrate and parallel to the area of the channel  $C_1$ .

The principal plane of the substrate is defined herein and throughout the remainder of the description as being a plane passing through the substrate and parallel to the  $[O; \vec{i}; \vec{j}]$  plane of the  $[O; \vec{i}; \vec{j}; \vec{k}]$  coordinate system shown in FIG. 1.

The area of the channel  $C_1$  of the transistor  $T_1$  is arranged on and in contact with an area of said insulating layer based on a dielectric material **102** with dielectric constant  $k_1$  and separated from the support layer **100** by this area.

The area of the insulating layer **101** separating the channel  $C_1$  from the support layer **100** is designed in this example to have a composition and thickness such that capacitive coupling can be set up between the channel  $C_1$  and said semiconducting support layer. This coupling may be such that a variation of the potential applied on the layer **100** causes a variation in the threshold voltage  $V_{T1}$  of the transistor  $T_1$ , for example of the order of 100 mV.

The insulating layer **101** may for example be based on  $\text{SiO}_2$  and its thickness may be less than 20 nm.

In a second region of the substrate separated from the first region by shallow trench isolation STI type trenches **160**, a different type of transistor  $T_2$  for example a transistor commonly called a “finFET” or of the type commonly called “triGate” comprises a channel  $C_2$  formed from a plurality of semiconducting bars or nanowires made by etching said thin semiconducting layer **104**, and that are therefore adjacent in a plane parallel to the principal plane of the substrate. The gate  $G_2$  of this transistor  $T_2$  has an encasing structure and it covers the lateral faces (in this example faces orthogonal to the  $[O; \vec{i}; \vec{k}]$  plane) and the top face of the nanowires (in this example a face parallel to the  $[O; \vec{i}; \vec{j}]$  plane).

The channel  $C_2$  of the transistor  $T_2$  is arranged on and in contact with an area based on a dielectric material **142** different from the material **102** in the area facing which the first transistor  $T_1$  is located with a dielectric constant  $k_2$  such that  $k_2 > k_1$ .

The area of dielectric material **142** separating the channel  $C_2$  from the support layer **100** in this example is designed to have a composition and thickness that enable capacitive coupling between this channel  $C_2$  and said semiconducting support layer.

The dielectric constant  $k_2$  of the dielectric material **142** is greater than the dielectric constant  $k_1$  of the dielectric material **102** to enable better capacitive coupling between the channel  $C_2$  and the substrate.

The area of the dielectric material **142** may for example be based on  $\text{Si}_3\text{N}_4$  or a high-k type dielectric material such as  $\text{HfO}_2$  or  $\text{HfSiO}_x\text{N}_y$ , with a thickness less than 25 nm or 20 nm.

Capacitive coupling between the channel  $C_2$  and the substrate is such that a modulation of the threshold voltage may be applied. Modulation occurs as soon as the order of magnitude of capacitive coupling between the channel and the substrate becomes the same as the order of magnitude of coupling between the gate and the channel, the substrate then acting as a second gate.

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Coupling between the channel  $C_2$  and the layer **100** may be such that a variation of potential applied on the layer **100** leads to a variation of the threshold voltage  $V_{T2}$  of the transistor  $T_2$  that can be as high as a few tens of mV, for example 100 mV.

FIG. 7 gives an example of a curve **710** of the variation of a parameter commonly called the “body factor” corresponding to a variation of the threshold voltage of a transistor with an arrangement similar to that of transistor  $T_2$  but with a single semiconducting bar with a height of the order of 15 nm, a width of the order of 15 nm, depending on a variation of the potential of the layer **100** of the substrate obtained in a case in which the dielectric material **142** is made of silicon nitride with a dielectric constant  $k=7$ . For comparison, a curve **720** illustrates the variation of the body factor for this transistor when the dielectric material **142** is replaced by  $\text{SiO}_2$ .

Such a device type may be applied to producing of a high performance low consumption logic circuit.

An example of a method for producing a transistor micro-electronic device will be described with reference to FIGS. 2A-2O (in which the device being produced is shown in a cross-sectional view XX'), FIGS. 3A-3L (in which the device being produced is represented in a top view), and FIGS. 4A-4J (in which the device currently being manufactured is shown in a cross-sectional view Y'Y or Z'Z).

The initial material for this method (FIG. 2A) may be a semiconductor on insulator type substrate formed from the support layer **100** based on a semiconducting material, for example silicon, the support layer being covered by the insulating layer **101** based on dielectric material **102** with a dielectric constant  $k_1$ , for example  $\text{SiO}_2$ , itself covered with the thin semiconducting layer **104**.

In particular, the insulating layer **101** may be a thin or ultra-thin layer of the type commonly called “thin-BOX” (Buried Oxide) or “ultra-thin BOX” (UTB), and thus be less than several tens of nanometers thick, or less than 20 nm, for example of the order of 10 nm.

The thin semiconducting layer **104** may for example be based on Ge or SiGe, or Si, particularly with an  $\langle 100 \rangle$  or  $\langle 110 \rangle$  orientation and with a thickness that may be less than 20 nm, for example of the order of 12 nm.

In a first region A of the substrate, and particularly of the layer **104**, at least one transistor of a given type, for example of the “finFET” or “trigate” type, provided with a channel in the form of several adjacent parallel bars will be made, while in one or several other regions (not shown in FIG. 2A), one or several different types of transistors, for example of the planar gate structure type will be formed.

Firstly, a first mask **106** is formed on the substrate **100** comprising an opening **107** delimiting the first region A and exposing the thin semiconducting layer **104**.

For example, the first mask **106** may be based on silicon nitride and its thickness may for example be between several nanometers and several tens of nanometers, for example of the order of 30 nm (FIGS. 2B and 3A).

The next step is to form a so-called “hard mask” layer **109**, for example based on a metal such as TiN so as to cover the first mask **106** and the first region A of the thin semiconducting layer **104** exposed through the opening **107**, in a conforming manner. The thickness of the hard mask layer **109** is between several nanometers and several tens of nanometers, for example of the order of 10 nm (FIG. 2C).

Then (FIGS. 3B, 2D, and 4A), a sacrificial block is made for example by deposition of a stack of a carbon based layer made by SoC (Spin On Carbon) deposition and Si-Arc and a resin that may for example be insulated using an electron beam (“e-beam”) that will be etched later.

The sacrificial block is composed of first parallelepiped shaped pads **110a**, **110b**, **110c**, **110d**, **110e** parallel and adjacent to each other, these first pads extending along a first direction (the first direction in this example being the direction of the vector  $\vec{i}$  or the coordinate system  $[O; \vec{i}; \vec{j}; \vec{k}]$  given in FIGS. 3B and 2D) parallel to the principal plane of the substrate. The sacrificial block is also composed of two parallelepiped pads **110<sub>1</sub>**, **110<sub>2</sub>**, joining the ends of the first pads **110a**, **110b**, **110c**, **110d**, **110e**, and extending along a second direction (in this example the direction of the vector  $\vec{j}$ ), orthogonal to said first direction.

Some pads **110a**, **110b**, **110c** have a portion formed facing the opening **107** of the mask **106** exposing the first region A of the thin semiconducting layer **104**, while the other blocks **110d**, **110e**, **110<sub>1</sub>**, **110<sub>2</sub>** are arranged around said first region A and facing the mask **106**.

The critical dimension  $Dc_1$  of the pads **110a**, **110b**, **110c**, **110d**, **110e**, **110<sub>1</sub>**, **110<sub>2</sub>** forming the sacrificial block may for example be of the order of 20 nm (the critical dimension being defined in this case and throughout this description as being the smallest dimension of an element measured in a plane parallel to the principal plane of the substrate, i.e. parallel to the  $[O; \vec{i}; \vec{j}]$  plane given for example in FIG. 3B).

The next step is to make a conforming deposition of a material **121** that may be dielectric, and for example based on silicon nitride and in particular covers the flanks or side faces of these pads **110a**, **110b**, **110c**, **110d**, **110e**, and **110<sub>1</sub>**, **110<sub>2</sub>**. The thickness of the deposited material **121** may for example be of the order of 10 nm.

Mask blocks **123** also called "spacers" **123** are formed by partial removal of the material **121** in contact with the side flanks of the sacrificial block and surrounding it. The critical dimension  $Dc_2$  of these spacers **123** may for example be of the order of about ten nanometers, less than the critical dimension  $Dc_1$  of the pads forming the sacrificial block and that may be approximately equal to the deposited thickness of the material **121** (FIGS. 3C, 2E, 4B). The spacers **123** may be made by etching and stopping on the hard mask layer **109**. For example, in this case, in which the spacers **123** are based on nitride and the hard mask layer **109** is based on metal such as TiN, this etching may be done by means for example of a  $N_2O_2$  plasma.

The next step is removal of the sacrificial block, while the spacers **123** are kept (FIGS. 3D, 2F, 4C).  $O_2$  plasma etching may be done for this purpose.

The patterns of spacers **123** in the hard mask layer **109** are then reproduced (FIGS. 3E, 2G, 4D). Thus, hard mask blocks **125** are formed in this layer **109** prolonging the spacers **123**. These blocks **125** on which the spacers **123** are supported have dimensions and particularly a critical dimension, equal to approximately  $Dc_2$  of the spacers **123**. This step may be done using anisotropic etching of the hard mask layer **109**, for example using  $BCl_3/Cl_2$ . This thus exposes the first mask **106** again, together with the first region A of the thin semiconducting layer **104** of the substrate.

The blocks **125** on which the spacers **123** are placed form a second mask **126** arranged above the first mask **106**, of which portions are located facing and partially covering the opening **107** of the first mask **106**.

The next step can be to reproduce the patterns of the second mask **126** in the thin semiconducting layer **104** (FIGS. 3F, 2H, 4E), so as to form semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**, also called "wires" (or nanowires if their critical dimension is less than 1  $\mu m$ ), or "fins" with a critical dimension  $Dc_3$  less than  $Dc_2$ . The critical dimension  $Dc_3$  of

the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** can thus be such that  $Dc_3 \approx Dc_2$  and is of the order of several nanometers, for example of the order of 10 nm. The adjacent semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**, may be distributed for example at a pitch of the order of 35 nm.

In order to perform this step, anisotropic etching is done through the first mask **106** and the second mask **126** stopping on the thin insulating layer **101** of the substrate. This etching may be done for example using  $CF_4$  and  $HBr/O_2$ .

The second mask **126** can then be removed. To achieve this, the spacers **123** can firstly be removed (FIGS. 3G, 2I, 4F), for example by HF etching.

Then (FIGS. 3H, 2J, 4G), FIG. 4G in this case showing a cross sectional view ZZ' shown in FIG. 3H), the blocks **125** are removed from the hard mask layer **109** to keep only the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**.

The next step is to remove the thin insulating layer **101** of the substrate facing the first region A and through the opening **107** of the first mask **106** (FIGS. 3I, 2K, 4H). This removal may for example be done by chemical etching using HF. After this removal, a portion of the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** located in the first region A is exposed. The semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** are thus suspended and held in place by areas of the thin semiconducting layer **104** that are not etched and are located outside the first region A delimited by the opening **107** of the first mask **106**. The exposed portions of the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** have top face **131**, bottom face **132** and lateral face **133**, **134** exposed in line with opening **107**.

A dielectric material **142** different from the material **102** in the thin insulating layer **101** can then be deposited. The dielectric constant  $k_2$  of the dielectric material **142** may in particular be greater than the dielectric constant  $k_1$  of the thin insulating layer **101** of the substrate. For example, the deposited dielectric material **142** may be a silicon nitride or a type of material commonly called a "high-k" material. The deposition may possibly be made so as to fill in the opening **107** in the hard mask **106** and possibly surround the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**. In this case, a polishing step commonly called "planarisation" or CMP (Chemical Mechanical Polishing) is done to remove the dielectric material **142** located above the top face of the first mask **106** (FIGS. 3J, 2L, 4I).

The dielectric material **142** is then partially removed so as to expose the top face **131** and side faces **133**, **134**, of the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**.

This partial removal may possibly be done until the top face of the remaining areas of the thin insulating layer **101** is reached corresponding to the level of the bottom face **132** of the bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**. In this case, the thickness of the area of dielectric material **142** produced under and facing the bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**, is approximately the same as the thickness of the insulating layer **101**.

The remaining area of dielectric material **142** then replaces the region of the thin BOX insulating layer **101** that had previously been removed. The area of replacement dielectric material **142** extends particularly along the bars and its thickness and composition are designed to set up capacitive coupling between the substrate **100** and the bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**. The next step is to remove the first mask **106**, for example by HF (FIGS. 2M, 3K, 4J).

The next step is to form isolation areas, for example of the STI type around the first region A and other regions B and D of the thin semiconducting layer **104** in which other transistor structures were made or will be made.

The isolation areas may be made by the formation of trenches **106** around the regions A, B, D, and then by deposition of a dielectric material **161** such as SiO<sub>2</sub> in these trenches **160**.

FIG. **20** shows a first isolation area that separates the first region A in which the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** were made from a second region B in which planar gate structure transistors, for example of the FDSOI type, will be made or are being made.

A second isolation area separates the first region A from a third region D in which one or several other structures or components have been made or will be made.

The steps to deposit a gate dielectric and then a gate material on the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** and on the region B of the thin semiconducting layer **104**, can then be done followed by etching of this gate dielectric and this gate material.

The result is the formation of transistor gates, and particularly one or several planar type gates that extend parallel to the thin semiconducting layer **104** of the substrate in the second region B and at least one encasing gate arranged around the side faces **133**, **134** and on the top face of the semiconducting bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>**.

One variant embodiment is shown in FIGS. **5A-5C** and **6A-6B**.

For this variant, the initial material may be the semiconductor on insulator type substrate in the previously described example method, formed by the support layer **100** based on semiconducting material covered by the insulating layer **101** based on a dielectric material **102** with a dielectric constant  $k_1$ , itself covered with the thin semiconducting layer **104**.

In a first region A of the layer **104**, a given type of transistor, for example a "finFET" or "trigate" type transistor with a channel in the form of adjacent parallel bars will be made, while at least one different type of transistor, for example a planar gate structure type transistor, will be formed in another region B'.

The first step is to form a hard mask layer **201**, for example based on a TeOS type silicon oxide, on the thin semiconducting layer **104**.

A mask **203**, for example based on a photosensitive resin facing the first region A of the thin semiconducting layer **104** is then formed on the hard mask layer **203**, the other region B' being exposed (FIG. **5A**).

The next step is to etch the hard mask layer **201**, the thin semiconducting layer **104** and the insulating layer **101** through the mask **203**.

Thus, the insulating layer **101** in the other region B' of the substrate is removed, so as to expose an area of the support layer **101** located in this second region of the semiconductor on insulator type substrate (FIG. **5B**).

The resin mask **203** can then be removed, and a semiconducting region **204** can then be formed on the exposed area of the support layer **101**. This semiconducting region **204** may be made for example by epitaxial growth (FIG. **5C**).

In the other region B' of the substrate, the semiconducting region **204** thus forms a modified bulk substrate type region. This thus forms a semiconductor on insulator type substrate

that is modified comprising a semiconducting region **204** supported directly on the support layer **100**.

A method like that described above with reference to FIGS. **2A-2O**, **3A-3L**, **4A-4J** can then be used in order to form a transistor channel structure with bars **130<sub>1</sub>**, **130<sub>2</sub>**, **130<sub>3</sub>**, **130<sub>4</sub>**, **130<sub>5</sub>**, **130<sub>6</sub>** in the first region A (FIG. **6A**).

A transistor T<sub>2</sub> comprising a channel formed from a plurality of semiconducting bars formed on a area based on dielectric material **142** different from the dielectric material of the insulating layer **101** in the semiconductor on insulator type substrate can then be formed in the first region A.

A planar transistor structure T<sub>1</sub> for which the channel structure is located in the semiconducting region **204** is formed in the other region B'. The regions A and B' can be co-integrated with a third region D of the insulating semiconductor substrate of which the insulating layer **101** was kept intact. In this third region, a transistor T<sub>3</sub> for which the channel is provided in the thin semiconducting layer **104** of the substrate can be formed (FIG. **6B**).

The invention claimed is:

1. A microelectronic device comprising:

a substrate comprising a thin semiconducting layer supported on an insulating layer, said insulating layer being supported on a semiconducting support layer,

at least one first transistor of a first type comprising a region suitable for forming a channel, the region comprising one or several adjacent bars, arranged in and/or on said thin semiconducting layer and an encasing gate arranged on said bars and around side faces of said bars, said channel of said first transistor being arranged on an area based on a given dielectric material different from that of said insulating layer,

the composition and thickness of said given dielectric material facilitating capacitive coupling between said channel of said first transistor and said semiconducting support layer of said substrate and/or said given dielectric material with a dielectric constant  $k_2$  such that  $k_2 > k_1$ , where  $k_1$  is the dielectric constant of the insulating layer material.

2. The microelectronic device according to claim 1, comprising at least one other transistor, the channel area of which is formed in a semiconducting region arranged on and in contact with the semiconducting support layer of the substrate.

3. The microelectronic device according to claim 1, said area of said insulating layer being based on SiO<sub>2</sub> and being less than 20 nm thick.

4. The microelectronic device according to claim 3, comprising at least a second transistor of which the channel area is formed in a region of the thin semiconducting layer arranged on and in contact with the insulating layer of the substrate.

5. The microelectronic device according to claim 4, the thickness and composition of said insulating layer facilitating a capacitive coupling between the channel of said second transistor and said semiconducting support layer of said substrate.

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